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November 2013

FDT1600N10ALZ

N-Channel PowerTrench® MOSFET 100 V, 5.6 A, 160 m Ω

Features

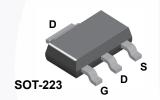
- $R_{DS(on)}$ = 121 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 2.8 A
- $R_{DS(on)}$ = 156 m Ω (Typ.) @ V_{GS} = 5 V, I_D = 1.8 A
- Low Gate Charge (Typ. 2.9 nC)
- Low C_{rss} (Typ. 2.04 pF)
- · Fast Switching
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

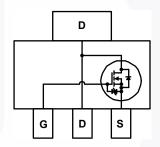
Description

This N-Channel MOSFET is produced using Fairchld Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance and maintain superior switching performance.

Application

- · Consumer Appliances
- · LED TV and Monitor
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25 °C unless otherwise noted.

Symbol	Parameter			FDT1600N10ALZ	Unit
V _{DSS}	Drain to Source Voltage			100	V
V _{GSS}	Gate to Source Voltage		±20	V	
I _D	Drain Current	- Continuous (T _C = 25 °C)		5.6	
		- Continuous (T _C = 100 °C)		3.5	A
I _{DM}	Drain Current	- Pulsed	(Note 2)	11.2	Α
E _{AS}	Single Pulse Avalanche Energy (Note 3)		9.2	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 4)		6.0	V/ns	
P_{D}	Dayyar Dissination	(T _C = 25 °C)	(T _C = 25 °C)		W
	Power Dissipation	- Derate Above 25 °C	- Derate Above 25 °C		°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	(Note 1)	12	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	(Note 1a)	60	C/VV

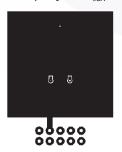
Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDT1600N10ALZ	16010ALZ	SOT-223	Tape and Reel	13"	12 mm	4000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted.

Symbol	Parameter	Test Con	Min	Тур	Max	Unit	
Off Chara	acteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V		100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		-	0.1	-	V/°C
I _{DSS} Zero Gate Voltage Drain Current		V _{DS} = 80 V, V _{GS} = 0V V _{DS} = 80 V, V _{GS} = 0V, T _C = 125 °C		-	-	1	μА
				-	-	500	
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V		-	-	±10	μΑ
On Chara	ecteristics				•		
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 25$	0 μΑ	1.4	-	2.8	V
	V _{CS} = 10 V. I _D = 2.8 A			-	121	160	mΩ
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 5 \text{ V}, I_D = 1.8$		-	156	375	mΩ
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 5.6 \text{ A}$		-	26.1	-	S
	Characteristics						
C _{iss}	Input Capacitance			-	169	225	pF
C _{oss}	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	43	55	pF
C _{rss}	Reverse Transfer Capacitance			-	2.04	-	pF
C _{oss(er)}	Energy Related Output Capacitance	V _{DS} = 50 V, V _{GS} =	O V	-	85	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{GS} = 10 V	V _{DD} = 50 V,	-	2.9	3.77	nC
Q _{g(tot)}	Total Gate Charge at 5V	V _{GS} = 5 V	I _D = 5.6 A	-	1.6	2.08	nC
Q _{gs}	Gate to Source Gate Charge			-	0.7	-	nC
Q _{qd}	Gate to Drain "Miller" Charge			-	0.64	-	nC
V _{plateau}	Gate Plateau Volatge		(Note 5)	-	3.81	-	V
Q _{sync}	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}, I_{D} = 2.8$	A	-	2.45	-	nC
Q _{oss}	Output Charge	V _{DS} = 50 V, V _{GS} = 0 V		-	5.2	-	nC
ESR	Equivalent Series Resistance(G-S)	f = 1 MHz		-	2.1	-	Ω
Switching	g Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 5.6	3 A	-	7.4	24.8	ns
t _r	Rise Time	$V_{DD} = 30 \text{ V}, I_D = 3.0 \text{ A},$ $V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$		-	2.5	15	ns
t _{d(off)}	Turn-Off Delay Time			- /	13.5	37	ns
t _f	Turn-Off Fall Time		-/	2.4	14.8	ns	
•	urce Diode Characteristics				1	1	
I _S	Maximum Continous Drain to Source Diode Forward Current			_	-	5.6	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	-	11.2	Α
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 5.0$	6A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 5.6		-	34.1	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	32.7	-	nC	

 R_{BUC} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BUC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a) 60 °C/W when mounted on a 1 in² pad of 2-oz copper.



b) 118 °C/W when mounted on a minimum pad of 2 oz copper.

^{2.} Repetitive rating: pulse-width limited by maximum junction temperature.
3. Starting T $_J$ = 25 °C, L = 3 mH, I_{AS} = 2.47 A.
4. $I_{SD} \leq$ 5.6 A, di/dt \leq 200 A/µs, $V_{DD} \leq$ BV $_{DSS}$, starting T $_J$ = 25°C.
5. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

10

V_{GS} = 15.0V

10.0V

8.0V

6.0V

5.0V

1. 250µs Pulse Test
4.5V
4.0V
2. T_C = 25°C
3.5V

V_{DS}, Drain-Source Voltage[V]

Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

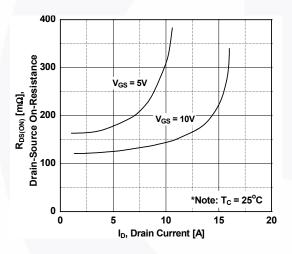


Figure 5. Capacitance Characteristics

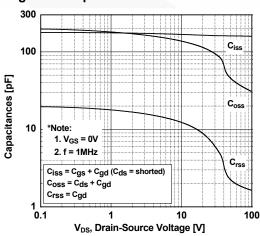


Figure 2. Transfer Characteristics

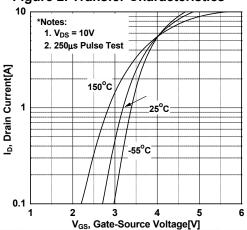


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

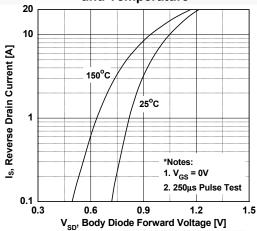
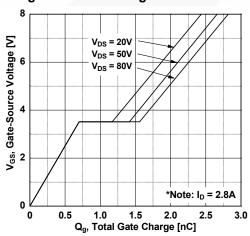


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

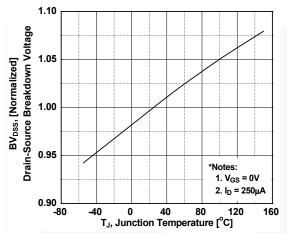


Figure 9. Maximum Safe Operating Area

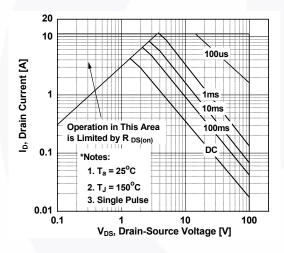


Figure 11. Eoss vs. Drain to Source Voltage

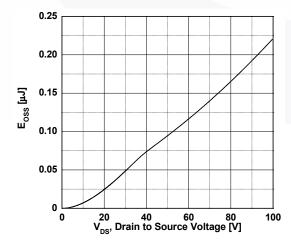


Figure 8. On-Resistance Variation vs. Temperature

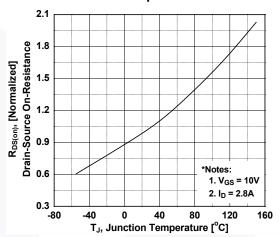


Figure 10. Maximum Drain Current vs. Case Temperature

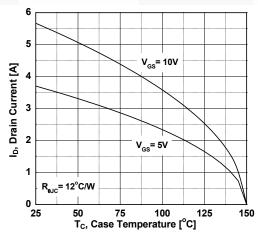
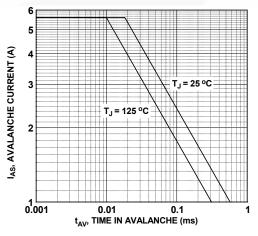
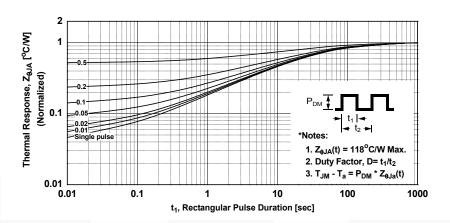


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)





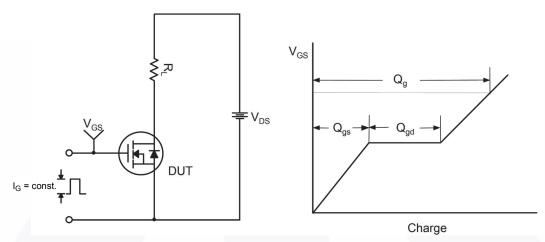


Figure 14. Gate Charge Test Circuit & Waveform

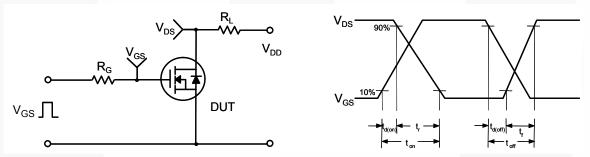


Figure 15. Resistive Switching Test Circuit & Waveforms

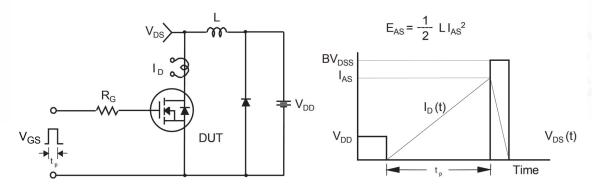


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

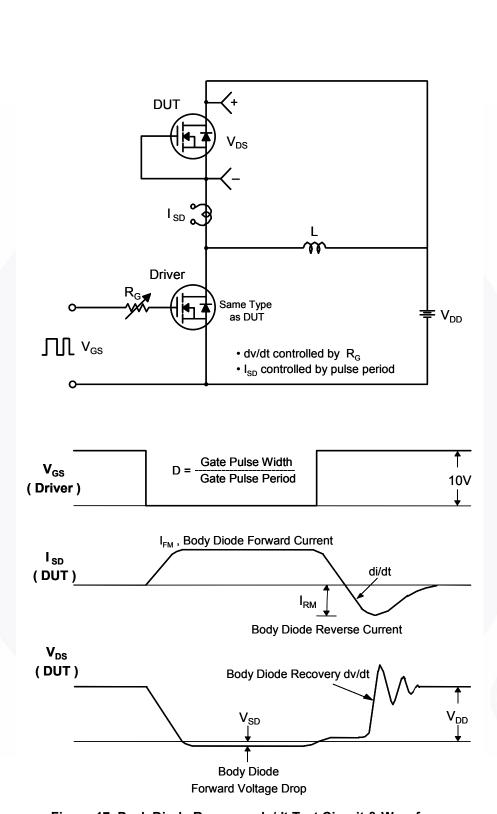


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

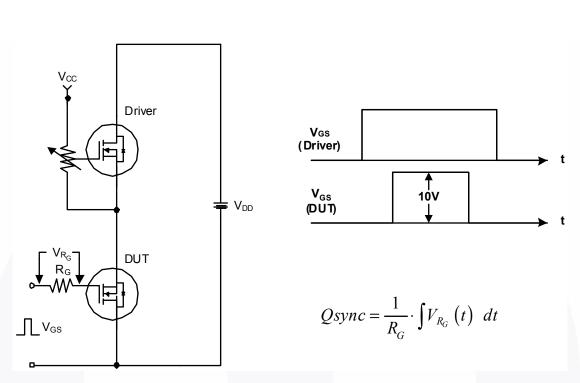


Figure 18. Total Gate Charge Qsync. Test Circuit & Waveforms

Mechanical Dimensions

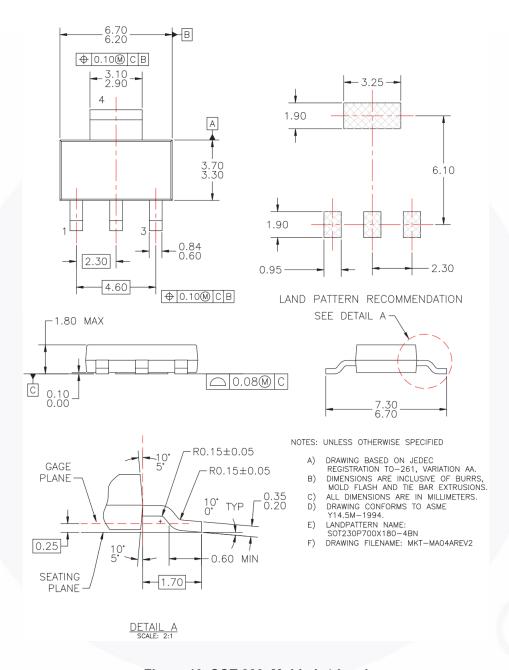


Figure 19. SOT-223, Molded, 4-Lead

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